NSN 5961-01-080-1888

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Inclosure Material:

Metal

Overall Length:

Between 0.250 inches and 0.340 inches

Overall Diameter:

0.620 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

-80.0 breakdown voltage, collector-to-base, emitter open and -80.0 breakdown voltage, collector-to-emitter, base open and -6.0

breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

Between -4.00 amperes source cutoff current and -10.00 amperes source cutoff current

Power Rating Per Characteristic:

20.0 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: pnp

Test Data Document:

45413-134814 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

- 1 case and 2 pin Shelf Life: N/a Unit Of Measure: --Demilitarization: No Fiig:
- A110a0